



STV240N75F3

N-channel 75 V, 2.3 mΩ, 240 A PowerSO-10
STripFET™ III Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} max	I _D
STV240N75F3	75 V	< 2.6 mΩ	240 A

- Conduction losses reduced
- Low profile, very low parasitic inductance

Application

- Switching applications

Description

This STripFET™ III Power MOSFET technology is among the latest improvements, which have been especially tailored to minimize on-state resistance providing superior switching performances.

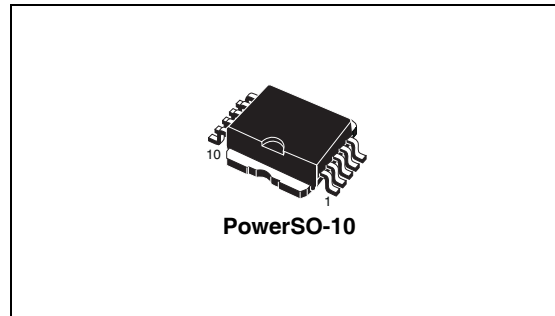


Figure 1. Internal schematic diagram and connection diagram (top view)

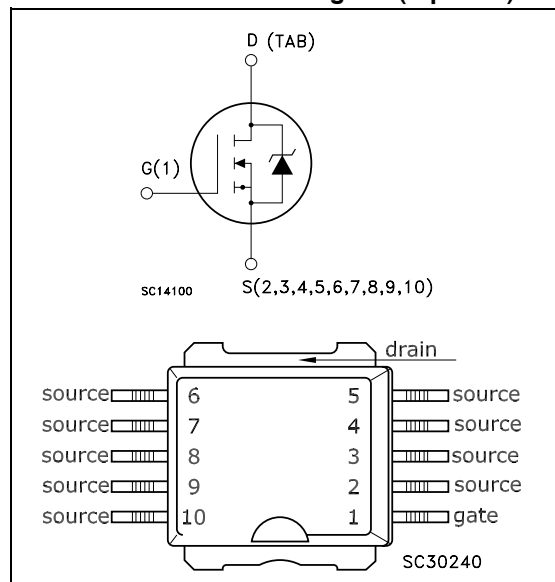


Table 1. Device summary

Order code	Marking	Package	Packaging
STV240N75F3	240N75F3	PowerSO-10	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	75	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	240	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	170	A
$I_{DM}^{(1)}$	Drain current (pulsed)	960	A
$P_{TOT}^{(2)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	300	W
	Derating factor	2.0	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	600	mJ
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_J	Operating junction temperature		$^\circ\text{C}$

1. Pulse width limited by safe operating area
2. This value is rated according to R_{thj-c}
3. Starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = 60\text{ A}$, $V_{DD} = 15\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	35	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch² FR-4 2 oz Cu.

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	75			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating}$, $T_C = 125\text{ °C}$			10 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{DS} = \pm 20\text{ V}$			± 200	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 120\text{ A}$		2.3	2.6	$\text{m}\Omega$

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance			6800		pF
C_{oss}	Output capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	1100	-	pF
C_{rss}	Reverse transfer capacitance					
Q_g	Total gate charge	$V_{DD} = 37.5\text{ V}$, $I_D = 120\text{ A}$,		85		nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{ V}$		30		nC
Q_{gd}	Gate-drain charge	(see Figure 14)		26		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 37.5 \text{ V}$, $I_D = 60 \text{ A}$ $R_G = 4.7 \Omega$, $V_{GS} = 10 \text{ V}$, (see Figure 13)	-	25 70	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD} = 37.5 \text{ V}$, $I_D = 60 \text{ A}$ $R_G = 4.7 \Omega$, $V_{GS} = 10 \text{ V}$, (see Figure 13)	-	100 15	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		240	A
$I_{SD}^{(1)}$	Source-drain current (pulsed)		-		960	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 120 \text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 120 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$	-	80		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 20 \text{ V}$, $T_j = 150 \text{ }^\circ\text{C}$	-	180		nC
I_{RRM}	Reverse recovery current	(see Figure 18)	-	4.5		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

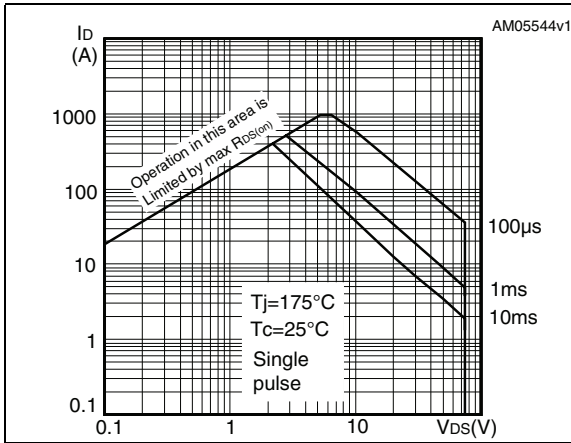


Figure 3. Thermal impedance

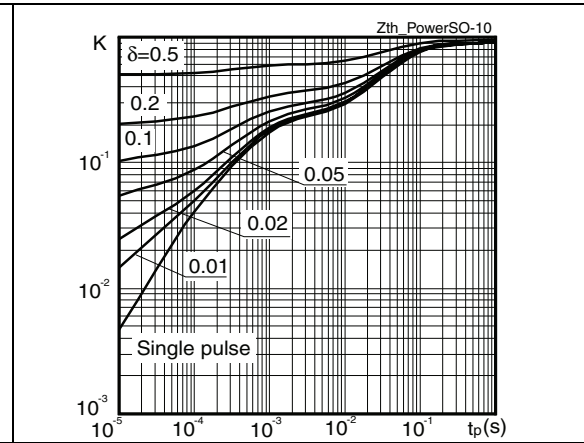


Figure 4. Output characteristics

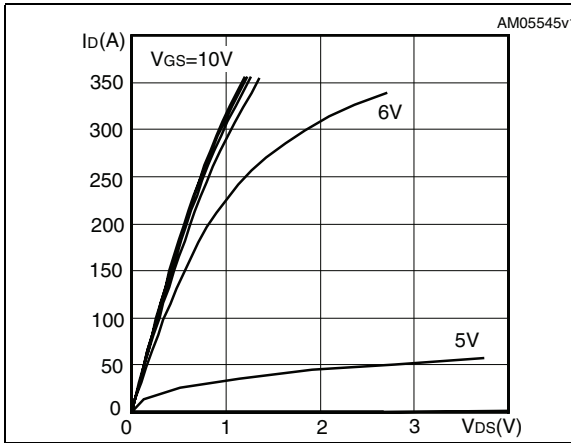


Figure 5. Transfer characteristics

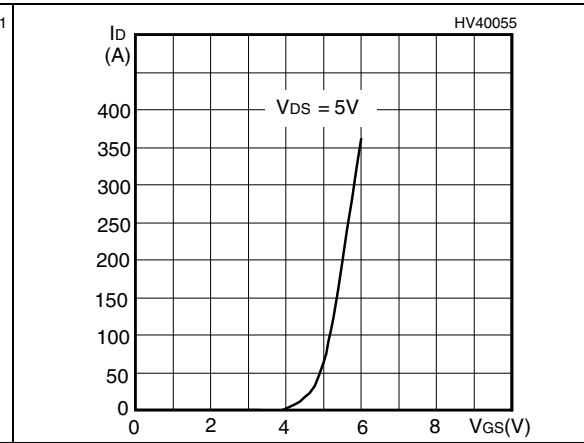


Figure 6. Normalized BV_{DSS} vs temperature

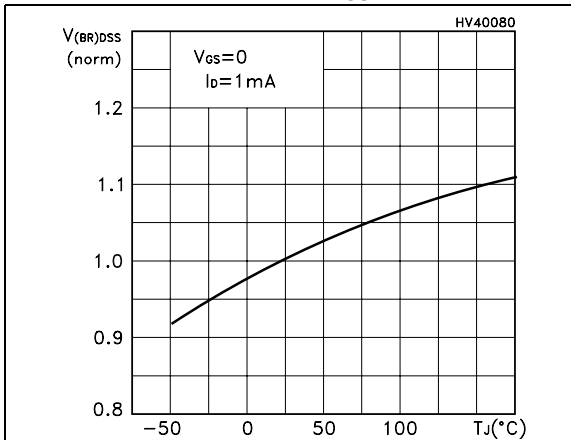


Figure 7. Static drain-source on resistance

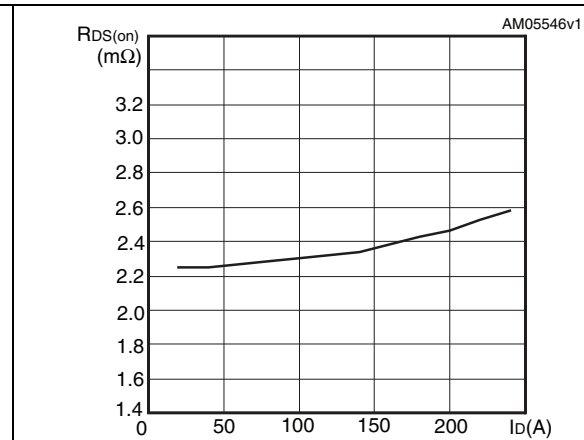


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

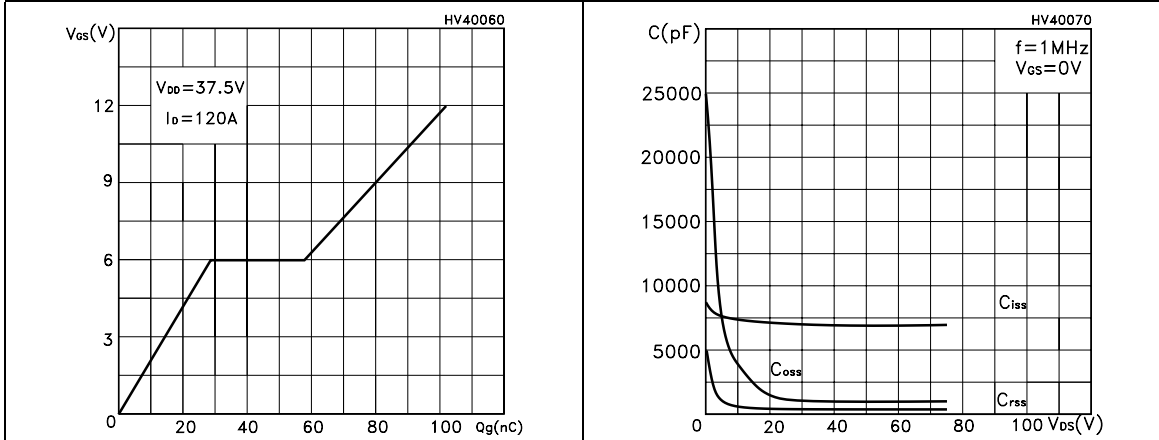


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

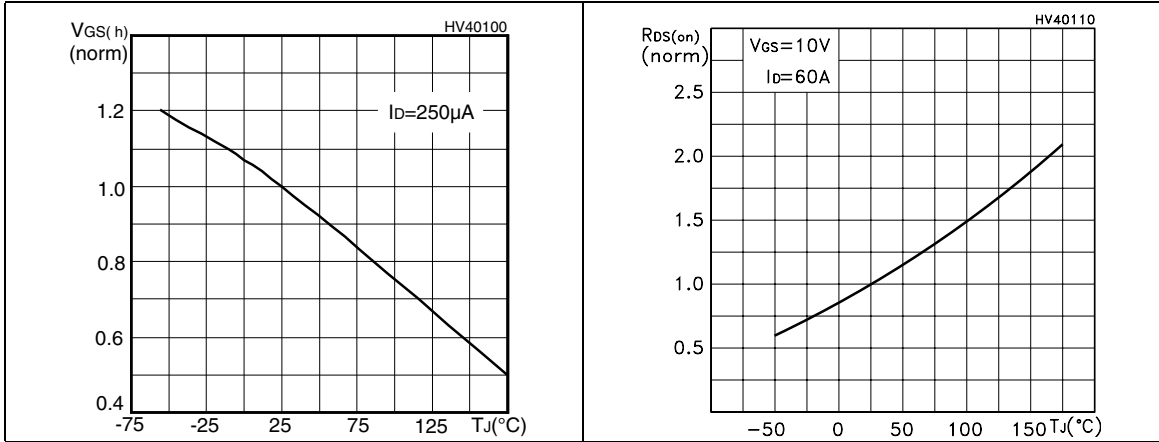
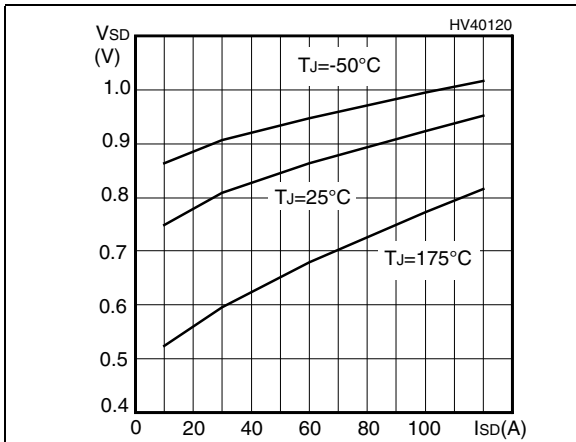


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

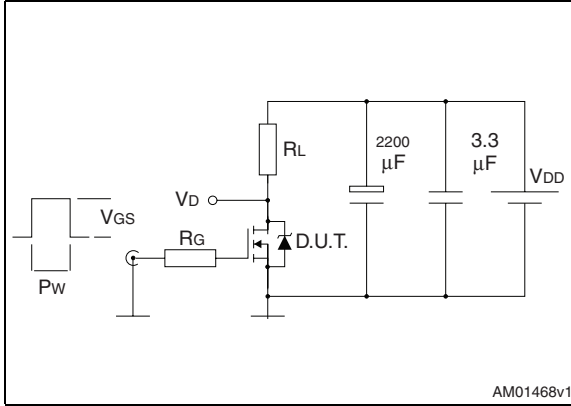


Figure 14. Gate charge test circuit

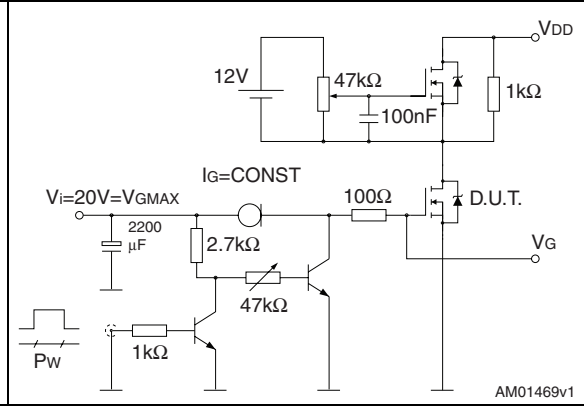


Figure 15. Test circuit for inductive load switching and diode recovery times

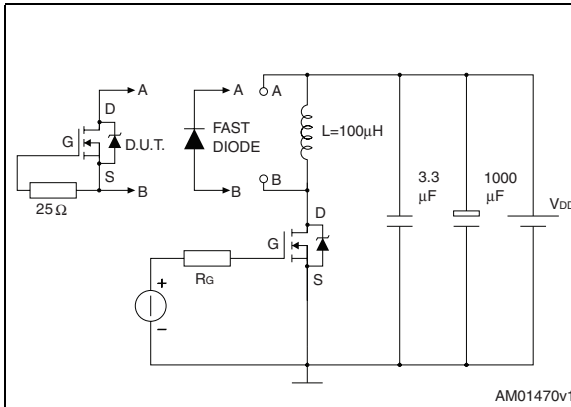


Figure 16. Unclamped inductive load test circuit

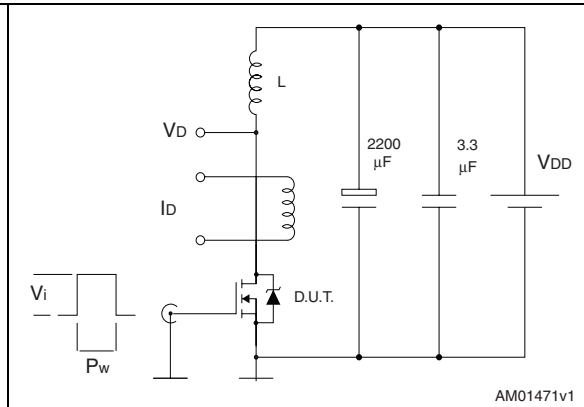


Figure 17. Unclamped inductive waveform

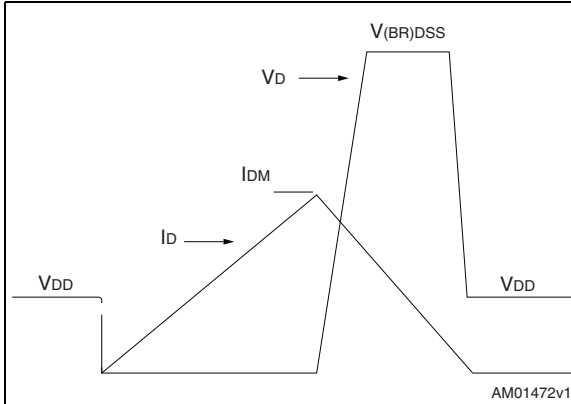


Figure 18. Switching time waveform

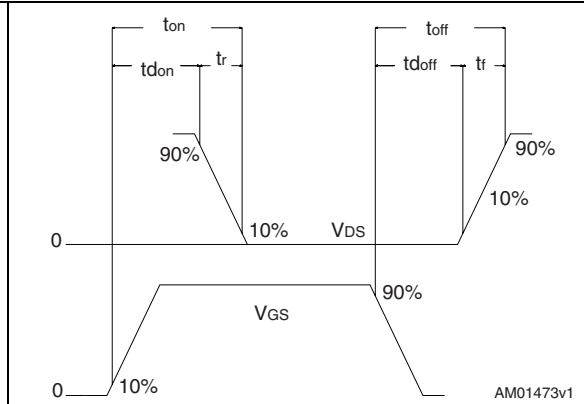


Figure 19. Gate charge test waveform

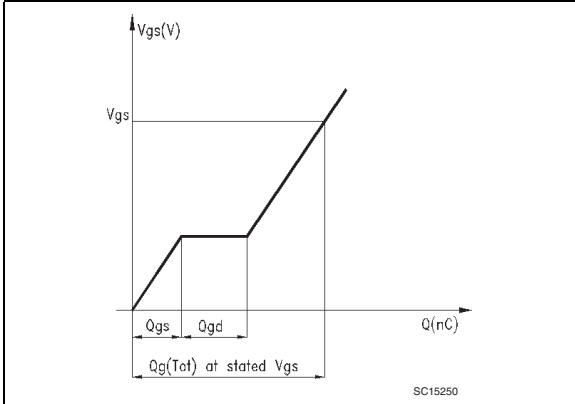
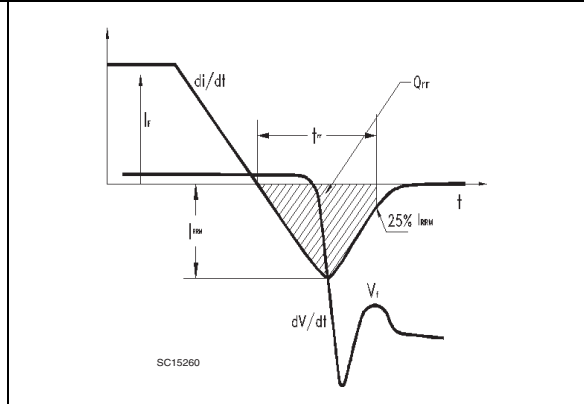


Figure 20. Diode recovery times waveform

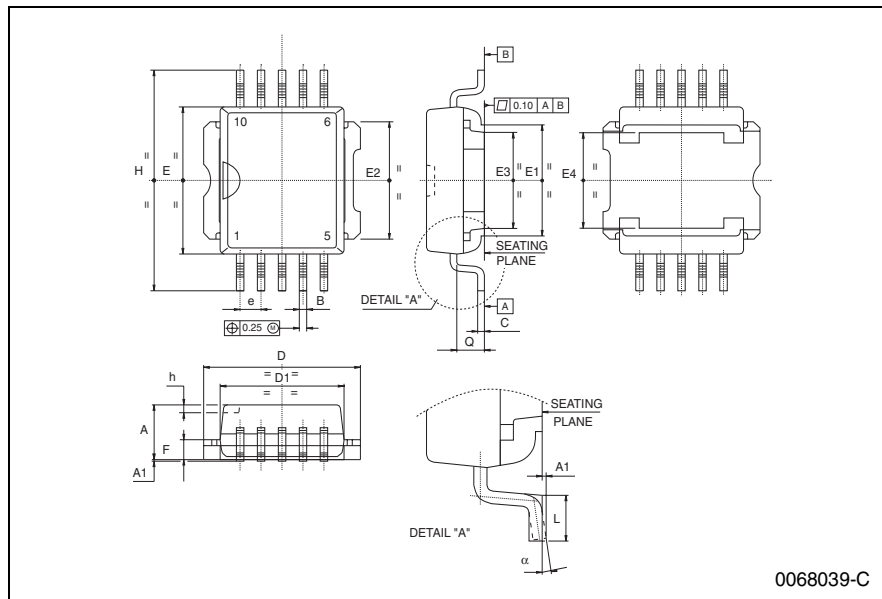


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

PowerSO-10 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	3.35		3.65	0.132		0.144
A1	0.00		0.10	0.000		0.004
B	0.40		0.60	0.016		0.024
C	0.35		0.55	0.013		0.022
D	9.40		9.60	0.370		0.378
D1	7.40		7.60	0.291		0.300
e		1.27			0.050	
E	9.30		9.50	0.366		0.374
E1	7.20		7.40	0.283		0.291
E2	7.20		7.60	0.283		0.300
E3	6.10		6.35	0.240		0.250
E4	5.90		6.10	0.232		0.240
F	1.25		1.35	0.049		0.053
h		0.50			0.002	
H	13.80		14.40	0.543		0.567
L	1.20		1.80	0.047		0.071
q		1.70			0.067	
α	0°		8°			



5 Packaging information

5.1 Tape and reel for PowerSO-10

Table 8. Carrier tape dimensions

Ref.	mm		
	Min.	Typ.	Max.
A0	14.9	15.0	15.1
B0	9.9	10.0	10.1
K0	4.15	4.25	4.35
F	11.4	11.5	11.6
E	1.65	1.75	1.85
W	23.7	24.0	24.3
P2	1.9	2.0	2.1
P0	3.9	4.0	4.1
P1	23.9	24.0	24.1
T	0.025	0.30	0.35
D(Ø)	1.50	1.55	1.60

Note: 10 sprocket hole pitch cumulative tolerance ± 0.2 mm.

Figure 21. Carrier tape drawing (a)

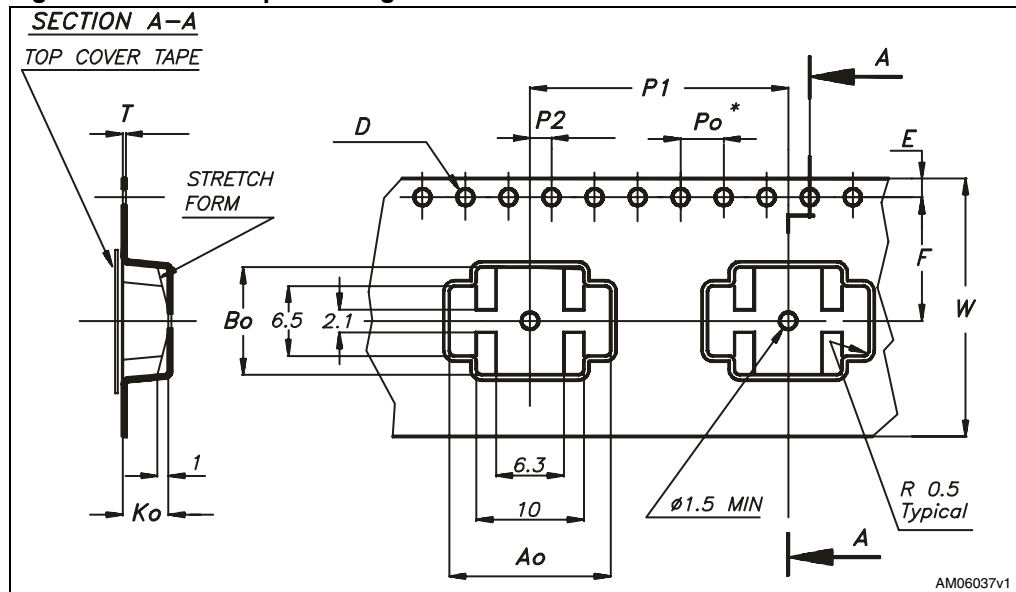


Table 9. Reel dimensions

Ref.	mm		
	Min.	Typ.	Max.
A			330
B	1.5		
C	12.8	13	13.2
D	20.2		
N	60		
G		24.4	
T			30.4

Note: 10 sprocket hole pitch cumulative tolerance ± 0.2 mm.

Figure 22. Reel drawing (b)

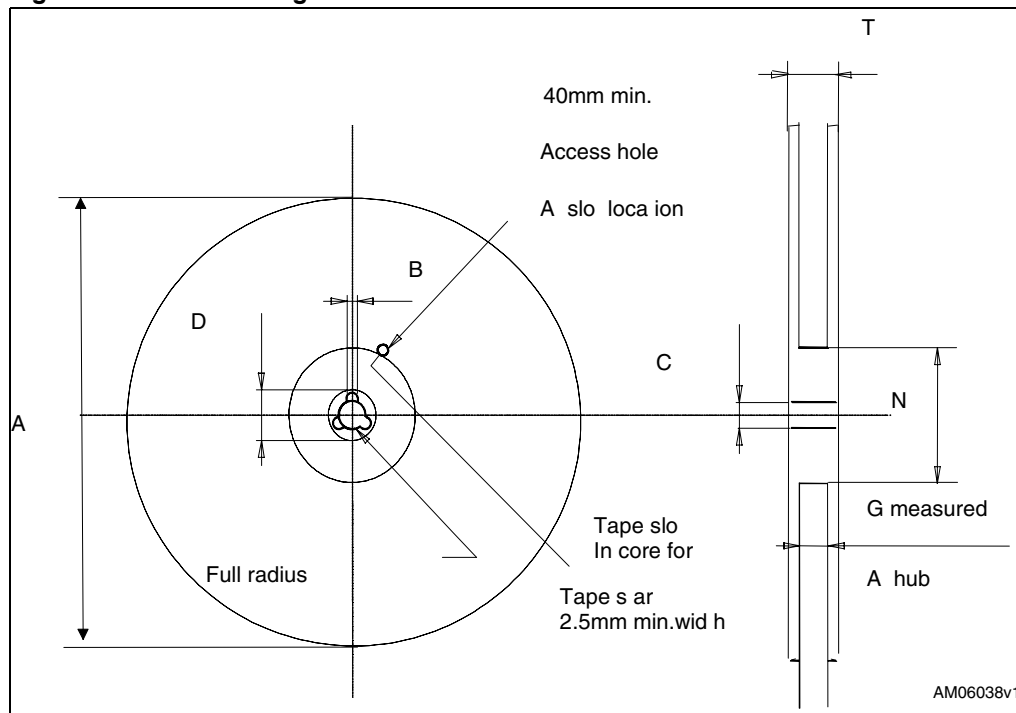


Table 10. Base and bulk quantities

Base qty.	Bulk qty.
	600

- a. Drawing is not to scale.
- b. Drawing is not to scale.

6 Revision history

Table 11. Document revision history

Date	Revision	Changes
02-Apr-2008	1	Initial release
21-Jan-2010	2	<ul style="list-style-type: none">– Document status promoted from preliminary data to datasheet.– Inserted new Section 5: Packaging information.

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